

11/13/01

JCS3 U.S. PTO

FEE TRANSMITTAL FOR FY 2002

Patent fees are subject to annual revision.

TOTAL AMOUNT OF PAYMENT

\$780.00

Attorney Docket No.

Complete if Known

Application Number to be assigned
 Filing Date November 13, 2001
 First Named Inventor Tetsuyoshi INOUE
 Examiner Name to be assigned
 Group Art Unit to be assigned
 204552021100

JCS3 U.S. PTO
09/08/01

11/13/01

METHOD OF PAYMENT

1. ☒ The Commissioner is hereby authorized to charge indicated fees and credit any overpayments to:

Deposit Account Number 03-1952
 Deposit Account Name Morrison & Foerster LLP

- ☒ Charge Any Additional Fee Required Under 37 CFR 1.16 and 1.17
☐ Applicant claims small entity status. See 37 CFR 1.27

2. ☐ Payment Enclosed:

☐ Check ☐ Credit Card ☐ Money Order ☐ Other

FEE CALCULATION

1. BASIC FILING FEE

Large Fee Code	Entity Fee (\$)	Small Fee Code	Entity Fee (\$)	Fee Description	Fee Paid
101	740	201	370	Utility filing fee	740
106	330	206	165	Design filing fee	
107	510	207	255	Plant filing fee	
108	740	208	370	Rescue filing fee	
114	190	214	80	Provisional filing fee	

SUBTOTAL (1) (\$)740

2. EXTRA CLAIM FEES

Total Claims	Independent Claims	Extra Claims	Fee from below	Fee Paid
5	2	220*	x 18	\$--
2	3	3**	x 84	\$--

Multiple Dependent

-- x 280 = \$--

Large Fee Code	Entity Fee (\$)	Small Fee Code	Entity Fee (\$)	Fee Description
103	18	203	9	Claims in excess of 20
102	84	202	42	Independent claims in excess of 3
104	290	204	140	Multiple dependent claims, if not paid
109	84	209	42	**Rescued independent claims over original patent
110	18	210	9	**Rescued claims in excess of 20 and over original patent

SUBTOTAL (2) (\$)

** or number previously paid, if greater; For rescues, see above.

FEE CALCULATION (continued)

3. ADDITIONAL FEES

Large Fee Code	Entity Fee (\$)	Small Fee Code	Entity Fee (\$)	Fee Description	Fee Paid
105	130	205	65	Surcharge - late filing fee or oath	
127	50	227	25	Surcharge - late provisional filing fee or cover sheet	
139	130	139	130	Non-English specification	
147	2,520	147	2,520	For filing a request for ex parte reexamination	
112	920*	112	920*	Requesting publication of SIR prior to Examiner action	
113	1,840*	113	1,840*	Requesting publication of SIR after Examiner action	
115	110	215	55	Extension for reply within first month	
116	400	216	200	Extension for reply within second month	
117	920	217	460	Extension for reply within third month	
118	1,440	218	720	Extension for reply within fourth month	
128	1,950	228	980	Extension for reply within fifth month	
119	320	219	160	Notice of Appeal	
120	320	220	160	Filing a brief in support of an appeal	
121	280	221	140	Request for oral hearing	
138	1,510	138	1,510	Petition to institute a public use proceeding	
140	110	240	55	Petition to revive - unavoidable	
141	1,280	241	640	Petition to revive - unintentional	
142	1,280	242	640	Utility issue fee (or resissue)	
143	450	243	230	Design issue fee	
144	620	244	310	Plant issue fee	
122	130	122	130	Petitions of the Commissioner	
123	50	123	50	Petitions related to provisional applications	
126	180	126	180	Submission of Information Disclosure Sheet	
581	40	581	40	Recording each patent assignment per properties (times number of properties)	40
146	740	246	370	Filing a submission after final rejection (37 CFR § 1.129(a))	
149	740	249	370	For each additional invention to be examined (37 CFR § 1.129(b))	
179	740	279	370	Request for Continued Examination (RCE)	
169	900	169	900	Request for expedited examination of a design application	

Other fee (specify) 6 Advance copies of patents

*Reduced by Basic Filing Fee Paid

SUBTOTAL (3) (\$)40

SUBMITTED BY

Name (Print/Type) Barry E. Bretschneider

Registration No. (Attorney/Agent)

28,055

Complete if applicable

Telephone (202) 887-1545

Date November 13, 2001

Signature

[Signature]

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information on a separate document.

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND THIS INFORMATION TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

dc-287219

Transmitted

Application Data Sheet

Inventor Information

Inventor One Given Name: Tetsuyoshi
Family Name: INOUE
Name Suffix:
Postal Address Line One: 2-3-52-109, Nishimikurado
Postal Address Line Two:
City: Yamatotakada-shi
State or Province: Nara-ken, Japan
Postal or Zip Code:
Citizenship Country: Japan

Inventor Two Given Name: Kazunori
Family Name: MATSUBARA
Name Suffix:
Postal Address Line One: 537, Yakuoji,
Postal Address Line Two: Tawaramoto-cho,
City: Shiki-gun
State or Province: Nara-ken, Japan
Postal or Zip Code:
Citizenship Country:

Correspondence Information

Name Line One: Barry E. Bretschneider
Name Line Two: Morrison & Foerster LLP
Address Line One: 2000 Pennsylvania Avenue, N.W.
Address Line Two: Suite 5500
City: Washington
State or Province: DC
Postal or Zip Code: 20006-1888
Telephone: (202) 887-1545
Fax: (202) 263-8396
Electronic Mail: BBretschneider@mofo.com

Application Information

Title Line One: SEMICONDUCTOR LASER MANUFACTURING
Title Line Two: METHOD AND SEMICONDUCTOR LASER
Total Drawing Sheets: 7
Formal Drawing: Yes
Application Type: Utility
Docket Number: 204552021700

Representative Information

Representative Customer Number: 25227

Prior Foreign Applications

Foreign Application One: 2000-354191
Filing Date: November 21, 2000
Country: Japan
Priority Claimed: Yes

11/21/2000
2000-354191
Japan
Priority Claimed: Yes

SEMICONDUCTOR LASER MANUFACTURING METHOD AND SEMICONDUCTOR LASER

5 BACKGROUND OF THE INVENTION

[0001] The present invention relates to a manufacturing method for a semiconductor laser device assembled by using a die-bond paste excellent in mass productivity, and also to a semiconductor laser device.

10 [0002] Conventionally, there has been provided a semiconductor laser device, as shown in Fig. 7, in which a semiconductor laser chip 24 is die-bonded to a submount 23 provided on a stem 21, and further covered with a cap 25. A laser beam emitted from the semiconductor laser chip 24 is outputted through glass 26 provided in the cap 25. Then, a monitoring-use photodiode 22 on the stem 21 detects the light outputted from one side of the semiconductor laser chip 24 opposite to the glass 26 side to use the light for estimation of the intensity of the light emitted to the glass 26 side.

15 [0003] As another semiconductor laser device, there has also been provided an integrated semiconductor laser device called hologram laser as shown in Fig. 8. In this semiconductor laser device, a hologram device 34 is
20 integrated with a semiconductor laser device similar in

construction to that shown in Fig. 7. The semiconductor laser device using the hologram device 34 is used primarily as a light source for optical disks, in which case light emitted from a semiconductor laser chip 32 is applied to the optical disk via the hologram device 34. Then, light reflected from the optical disk is deflected and converged toward an OPIC photodetection chip 33 (photodetector in which a plurality of photodetection parts and signal processing circuits are integrated) by a diffraction effect with a hologram 34a formed on the surface of the hologram device 34, thereby detecting a signal recorded on the optical disk. The semiconductor laser chip 32 is die-bonded to a stem 31, whereas a submount for die-bonding use is omitted in Fig. 8 for simplicity' sake.

[0004] Figs. 9A - 9C are views for explaining a manufacturing method for semiconductor laser devices of Figs. 7 and 8, where Figs. 9A - 9C depict only a portion at which the semiconductor laser chip is die-bonded. As the brazing filler metal for die-bonding, metals good at heat conduction and electrical conduction such as gold - tin alloys, solder and indium are often used, but metallic brazing filler materials are unfortunately difficult to use because of their high melting temperatures, which are generally beyond 200°C. Further, brazing filler materials using indium, which is low in melting temperature, would

soften during use, causing the semiconductor laser chip to moved. Silver paste, which is an electrically conductive die-bond paste using metal, on the other hand, is easy to use even at room temperature by virtue of its paste form, and will cure at relatively low temperature of about 150°C. Even if exposed to high temperatures, silver paste, which indeed may cure, but will not soften, thus eliminating the problem that the semiconductor laser chip may be caused to move. Thus, silver paste has been widely used in recent years.

[0005] Now, a manufacturing method for a semiconductor laser device is described with reference to Figs. 9A - 9C.

[0006] First of all, as shown in Fig. 9A, a silver paste 42 is applied onto a stem 41 (or onto a submount) at room temperature.

[0007] Next, as shown in Fig. 9B, a semiconductor laser chip 43 is placed at a position where the silver paste 42 has been applied, and pressurized into a form of a semiconductor laser device. This pressurization is done in order to instantaneously purge out the silver paste that has entered into a gap between the semiconductor laser chip 43 and the stem 41 (or the submount).

[0008] Next, as shown in Fig. 9C, the semiconductor laser device fabricated at Fig. 9B is placed within thermostat 45 and then heating is performed to make the

silver paste 42 cured, by which die bonding is completed. Curing conditions for silver paste in this case are set to 150°C and about 1 hour.

[0009] The silver paste to be used for die bonding of the semiconductor laser device is so made by filling resin with silver powder given in such a form as needle crystals or flakes. Therefore, the silver paste has a drawback of being large in electrical resistance and thermal resistance, compared with metallic brazing filler materials. Particularly as to the thermal resistance, while semiconductor laser devices using indium as the brazing filler material has a thermal resistance of about 60°C/W, while semiconductor laser devices using silver paste has a thermal resistance of 100°C/W or higher, which has found to be problematic. Such high thermal resistances would make it difficult for heat generated at the active layer to transfer to the stem, causing the temperature of the active layer to increase more and more so that the semiconductor laser chip may fail.

[0010] Also, when heating is performed in the thermostat to make the silver paste cured so that the semiconductor laser chip is fixed onto the stem, the semiconductor laser chip is not held and the semiconductor laser chip is left only placed on the silver paste. As a result, silver paste interposed between the semiconductor laser chip and the

stem does not become uniform in thickness. This would lead to instability in the bonding state of the semiconductor laser chip and the stem, which in turn would lead to instability of electrical resistance, resulting in a problem of variations in operating current.

[0011] Further, there is a problem that the silver paste creeps up on side faces of the semiconductor laser chip so as to reach the active layer of the semiconductor laser chip, making the semiconductor laser chip short-circuited by the silver paste. This is due to the fact that whereas warming the whole semiconductor laser device in the thermostat makes the silver paste go creeping up, the height of the creep-up cannot be controlled.

[0012] Therefore, an object of the invention is to provide a manufacturing method for a semiconductor laser device, as well as a semiconductor laser device, which can be lowered in thermal resistance and reduced in variations of operating current and further prevented from short-circuiting of the semiconductor laser chip.

[0013] In order to achieve the above object, the present invention provides a manufacturing method for a semiconductor laser device in which a semiconductor laser chip is mounted on a base portion by using an electrically conductive die-bond paste using a metal, the method comprising the step of:

applying the conductive die-bond paste onto the base portion;

mounting the semiconductor laser chip onto the base portion on which the conductive die-bond paste has been applied;

heating the semiconductor laser chip mounted on the base portion while the semiconductor laser chip is kept pressurized toward the base portion, thereby temporarily curing the conductive die-bond paste; and

after the temporary curing, finally curing the conductive die-bond paste.

[0014] In this semiconductor laser device manufacturing method, the conductive die-bond paste (silver paste, copper paste or silver palladium paste, etc.) using a metal is applied to the base portion such as a stem, submount or wiring board, and the semiconductor laser chip is mounted onto the base portion on which the conductive die-bond paste has been applied. Then, the semiconductor laser chip, while kept pressurized toward the base portion, is heated to make the conductive die-bond paste temporarily cured, by which the semiconductor laser chip is fixed immobile to the base portion, and thereafter the conductive die-bond paste is finally cured. Since the conductive die-bond paste interposed between the semiconductor laser chip and the base portion can be maintained 5 μm or less thick

by pressurizing the semiconductor laser chip from above toward the base portion in the temporary curing step, a stable bonding state can be achieved. Therefore, the thermal resistance can be lowered and moreover the thermal resistance and the electrical resistance can be stabilized so that variations in operating current can be suppressed. Further, since the conductive die-bond paste has already become high in viscosity as a result of the temporary curing, the creep-up height of the conductive die-bond paste at the side face of the semiconductor laser chip from the die-bond surface can be made not more than 40 μm when the conductive die-bond paste is cured, for example, by heating the whole within the thermostat in the temporary curing step after the temporary curing step. Therefore, the creep-up of the conductive die-bond paste never becomes higher than the position of the active layer of the semiconductor laser chip, the semiconductor laser chip can be prevented from short-circuiting.

[0015] Also, there is provided a semiconductor laser device comprising a semiconductor laser chip mounted on a base portion by using an electrically conductive die-bond paste using a metal, wherein

thermal resistance of the semiconductor laser device is 90°C/W or lower.

00000000-11111111

[0016] In the case where the semiconductor laser chip is mounted onto the base portion by using the conductive die-bond paste using a metal, conventional die bond using, for example, silver paste would involve a thermal resistance of 100°C/W or higher, which is practically problematic in reliability. In contrast to this, in the semiconductor laser device of the above constitution, the thermal resistance of the semiconductor laser device in which the semiconductor laser chip is mounted on the base portion can be made 90°C/W or lower by using a conductive die-bond paste using a metal, by which heat generated at the active layer of the semiconductor laser chip can easily be purged toward the base portion via the conductive die-bond paste. Thus, a semiconductor laser device of high reliability can be obtained.

[0017] In one embodiment of the present invention, creep-up height of the conductive die-bond paste at a side face of the semiconductor laser chip from a die-bond surface of the semiconductor laser chip is not more than 40 μm .

[0018] In the semiconductor laser device of this embodiment, since the active layer of the semiconductor laser chip is generally positioned higher than at least 40 μm from the die-bond surface, the conductive die-bond paste can be made no higher than the position of the active layer

by the arrangement that the creep-up height of the conductive die-bond paste at the side face of the semiconductor laser chip from the die-bond surface is 40 μm or lower. Thus, the semiconductor laser chip can be prevented from short-circuiting.

[0019] In one embodiment of the present invention, the conductive die-bond paste interposed between a die-bond surface of the semiconductor laser chip and the base portion is 5 μm or lower thick.

[0020] In the semiconductor laser device of this embodiment, by the arrangement that the conductive die-bond paste interposed between the die-bond surface of the semiconductor laser chip and the base portion is made 5 μm or less thick, a stable bonding state between the die-bond surface of the semiconductor laser chip and the base portion can be achieved, allowing a stable electrical resistance to be obtained. Thus, operating variations can be reduced.

[0021] In one embodiment of the present invention, the conductive die-bond paste using a metal is silver paste.

[0022] In the semiconductor laser device of this embodiment, silver paste that is the conductive die-bond paste using a metal is pasty even at room temperature and curable at relatively low temperatures, thus being easy to handle. This allows the productivity to be improved.

BRIEF DESCRIPTION OF THE DRAWINGS

00337610-11301
5 [0023] The present invention will become more fully understood from the detailed description given hereinbelow and the accompanying drawings which are given by way of illustration only, and thus are not limitative of the present invention, and wherein:

10 [0024] Fig. 1 is a side view of main part of a semiconductor laser device which is an embodiment of the present invention;

[0025] Figs. 2A, 2B, 2C and 2D are views showing manufacturing steps for the semiconductor laser device;

15 [0026] Fig. 3 is a chart showing variations of operating current resulting while the semiconductor laser device is kept electrically conducting for a long time under laser oscillation;

20 [0027] Fig. 4 is a chart showing variations of operating current resulting while a semiconductor laser device of Comparative Example 1 is kept electrically conducting for a long time under laser oscillation;

[0028] Fig. 5 is a chart showing variations of operating current resulting while a semiconductor laser device of Comparative Example 2 is kept electrically conducting for a long time under laser oscillation;

[0029] Fig. 6 is a chart showing variations of operating current resulting while a semiconductor laser device of Background Art Example is kept electrically conducting for a long time under laser oscillation;

5 [0030] Fig. 7 is a fragmentary broken view of a semiconductor laser device according to the background art;

[0031] Fig. 8 is a fragmentary broken view of a semiconductor laser device using a hologram element according to the background art;

10 [0032] Figs. 9A, 9B and 9C are views showing manufacturing steps for the semiconductor laser device of the background art;

[0033] Figs. 10A, 10B and 10C are charts for explaining the method of measuring thermal resistance.

15

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0034] Hereinbelow, a semiconductor laser device manufacturing method as well as a semiconductor laser device according to the present invention are described in
20 detail by way of embodiments thereof illustrated in the accompanying drawings.

[0035] Fig. 1 is a side view of main part of a semiconductor laser device which is an embodiment of the present invention, where reference numeral 1 denotes a stem
25 as a base portion, 2 denotes silver paste as an

electrically conductive die-bond paste using a metal applied onto the stem 1, and 3 denotes a semiconductor laser chip mounted on the stem 1 via the silver paste 2.

5 [0036] Next, the manufacturing method for this semiconductor laser device is explained with reference to Figs. 2A, 2B, 2C and 2D.

10 [0037] First of all, as shown in Fig. 2A, the silver paste 2 is applied onto the stem 1. The silver paste 2 in this case is applied into a 0.15 mm-dia. dome shape, its volume being set to $1.77 \times 10^{-3} \text{ mm}^3$. The silver paste used in this case is T-3040 made by Sumitomo Kinzoku Kozan K.K. (silver content ratio: 82 - 84%).

15 [0038] Next, as shown in Fig. 2B, the semiconductor laser chip 3 is mounted on the stem 1 via the silver paste 2.

20 [0039] Next, as shown in Fig. 2C, the semiconductor laser chip 3 is temporarily cured, while pressurized toward a direction of arrow R by a collet 10, by heating the stem 1. The pressurization in this case is done by applying a 50 g weight (not shown) to the collet 10 having a diameter of about 0.2 mm. The heating process is carried out at temperatures of 200°C or higher for 10 seconds by measuring the temperature of the stem 1 (heat sink) by a thermocouple 11, where temperature increase and decrease are accelerated
25 as much as possible.

[0040] Then, as shown in Fig. 2D, the semiconductor laser device (1, 2, 3) over the temporary curing is heated within a thermostat 12 so as to be finally cured. Heating in this case is performed by setting the temperature in the thermostat 12 to 150°C and leaving the semiconductor laser device for 1 hour. Further, collectively curing a large amount of temporarily cured semiconductor laser devices makes it possible to maintain the curing time per device substantially short.

[0041] Table 1 given below shows experimental results of measuring creep-up amount and thermal resistance in the semiconductor laser devices of Example, Comparative Example 1, Comparative Example 2, and Background Art Example. In this experiment, the semiconductor laser device of Example is one fabricated by the above-described manufacturing method, and the semiconductor laser device of Comparative Example 1 is one fabricated by a pressurizing step under the same conditions as with Example in the steps of temporary curing, and a finally curing step without heating. Further, the semiconductor laser device of Comparative Example 2 is one fabricated through the steps of once setting up the chip with a collet in temporary curing step, then removing the collet into a no-pressure state, simultaneously performing a heating step under the same heating conditions as with Example, and thereafter

5

Table 1

Sample preparation method	Example		Comparative example 1		Comparative example 2		Background art example	
	Creep- up amount (μm)	Thermal resistance ($^{\circ}\text{C}/\text{W}$)	Creep- up amount (μm)	Thermal resistance ($^{\circ}\text{C}/\text{W}$)	Creep- up amount (μm)	Thermal resistance ($^{\circ}\text{C}/\text{W}$)	Creep- up amount (μm)	Thermal resistance ($^{\circ}\text{C}/\text{W}$)
Sample No.								
1	20	88.3	57	128.6	34	91.5	35	120.4
2	24	79.3	46	118.6	33	87.6	33	122.8
3	26	79.1	55	107.1	33	90.4	25	125.7
4	30	80.0	48	108.0	30	91.2	42	114.8
5	28	76.1	54	106.5	31	86.6	44	109.7
6	36	74.9	50	105.3	31	92.1	43	118.7
7	35	78.9	62	118.4	22	96.8	32	110.2
8	34	75.8	59	105.5	35	103.2	28	124.1
9	37	77.7	55	107.9	33	91.3	35	117.5
10	40	80.5			33	92.3		
Mean	31.0	79.1	54.0	111.8	31.5	92.3	35.2	118.2

Now the method of measuring the thermal resistance in the above experiment is explained with reference to Figs. 10A, 10B and 10C.

[0042] First, a semiconductor laser device is placed in a thermostat, and a forward voltage V_F resulting when a constant small current I_m is passed through the semiconductor laser device is measured. As shown in Fig. 10A, measurement is performed with temperature varied, by which temperature coefficient $M (= \Delta V_F / \Delta T)$ of V_F is measured. This measurement of temperature coefficient M does not need to be performed with individual semiconductor laser devices, but is done only once with a semiconductor laser device fabricated under the same conditions.

[0043] Next, as shown in Fig. 10B, such a small current I_m (about 5 mA or less) that heat generation of the semiconductor laser device is negligible is passed, and subsequently a forward current I_{F2} of several tens of mA is passed for a specified time T_P . A resulting forward voltage to the forward current I_{F2} in this case is assumed as V_{F2} .

[0044] Also, Fig. 10C shows variations in the forward voltage V_F , where the passage of the forward current I_{F2} causes the forward voltage to increase as well, which in turn causes the semiconductor laser chip to increase in temperature so that the forward voltage V_F decreases

exponentially and comes to a generally constant value during the measurement time TP. This resulting constant forward voltage is assumed as VF2. Also, when the forward current is lowered to Im, the forward voltage once comes to a value lower than VF1 and thereafter exponentially increases to return to the constant value. If the variation of the forward voltage in this case is assumed as ΔVF, then the thermal resistance Rth can be determined by an equation:

$$R_{th} = (\Delta VF/M) / (IF2 \times VF2) \quad (^\circ C/W).$$

[0045] From the results of Table 1 obtained in this way, it can be understood that Example can provide the lowest thermal resistance, which is at most 90°C/W or lower. Also, Example and Comparative Example 2 show smaller creep-up amounts, finding that the creep-up amount can be suppressed by the heating during the temporary curing step.

[0046] Furthermore, Figs. 3 to 6 show experiment results of measuring variations of operating current resulting while the semiconductor laser devices of Example, Comparative Example 1, Comparative Example 2 and Background Art Example are kept electrically conducting for a long time under laser oscillation. In Figs. 3 to 6, the horizontal axis represents conduction time and the vertical axis represents the operating current.

[0047] As apparent from Figs. 3 to 6, from the viewpoint of operating current where the conduction time is zero, Example of Fig. 3 shows the least variations, finding that a stable bonding state has been achieved. Example also
5 shows the least increase in operating current after a 150 hour conduction, exhibiting an effect of reduction in thermal resistance.

[0048] Thus, with the semiconductor laser device manufacturing method as shown above, since the silver paste
10 2 interposed between the semiconductor laser chip 3 and the stem 1 can be maintained 5 μm or less thick by pressurizing the semiconductor laser chip 3 from above toward the stem 1 side in the temporary curing step, a stable bonding state can be achieved so that the thermal resistance can be
15 lowered, and further that variations in operating current can be suppressed.

[0049] Further, since the creep-up amount of the silver paste 2 can be lessened by a short-time (10 seconds) heating at 200°C or higher in the temporary curing step of
20 Fig. 2C, the creep-up amount of the silver paste 2 can be suppressed small. Further, since the silver paste that has increased in viscosity due to this temporary curing is cured by heating the whole within the thermostat 12 in the final curing step of Fig. 2D, the creep-up amount can be
25 reduced more largely than the cases in which only the final

curing is involved. In this semiconductor laser device, since a creep-up height H2 (shown in Fig. 1) of the silver paste 2 at a side face of the semiconductor laser chip 3 from the die-bond surface can be made 40 μm or lower, the silver paste 2 never becomes higher than a height H1 from the die-bond surface to an active layer 4 of the semiconductor laser chip 3, so that the semiconductor laser chip 3 can be prevented from short-circuiting.

[0050] In the above embodiment, the semiconductor laser chip 3 is mounted on the stem 1 serving as a base portion. However, the present invention may be applied to semiconductor laser devices in which the semiconductor laser chip is mounted on such a base portion as a submount, printed circuit board or lead frame.

[0051] Further, although silver paste is used as a conductive die-bond paste using metal in the above embodiment, copper paste, silver palladium paste or the like may also be used.

[0052] The invention being thus described, it will be obvious that the same may be varied in many ways. Such variations are not to be regarded as a departure from the spirit and scope of the invention, and all such modifications as would be obvious to one skilled in the art are intended to be included within the scope of the following claims.

WHAT IS CLAIMED IS:

1. A manufacturing method for a semiconductor laser device in which a semiconductor laser chip is mounted on a base portion by using an electrically conductive die-bond paste using a metal, the method comprising the step of:

applying the conductive die-bond paste onto the base portion;

mounting the semiconductor laser chip onto the base portion on which the conductive die-bond paste has been applied;

heating the semiconductor laser chip mounted on the base portion while the semiconductor laser chip is kept pressurized toward the base portion, thereby temporarily curing the conductive die-bond paste; and

after the temporary curing, finally curing the conductive die-bond paste.

2. A semiconductor laser device comprising a semiconductor laser chip mounted on a base portion by using an electrically conductive die-bond paste using a metal, wherein

thermal resistance of the semiconductor laser device is 90°C/W or lower.

3. The semiconductor laser device according to Claim 2, wherein

creep-up height of the conductive die-bond paste at a side face of the semiconductor laser chip from a die-bond surface of the semiconductor laser chip is not more than 40 μm .

- 5 4. The semiconductor laser device according to Claim 2, wherein

 the conductive die-bond paste interposed between a die-bond surface of the semiconductor laser chip and the base portion is 5 μm or lower thick.

- 10 5. The semiconductor laser device according to Claim 2, wherein

 the conductive die-bond paste using a metal is silver paste.

5

10

Fig. 1

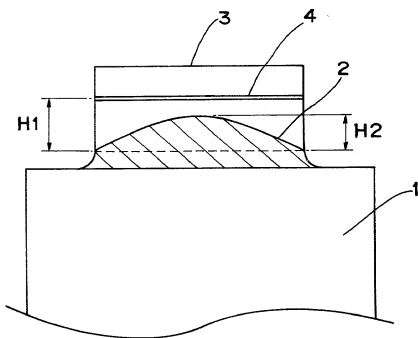


Fig.2A

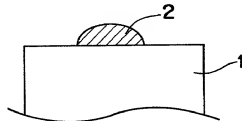


Fig.2B

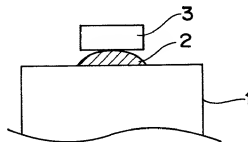


Fig.2C

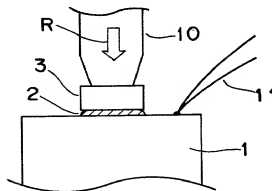


Fig.2D

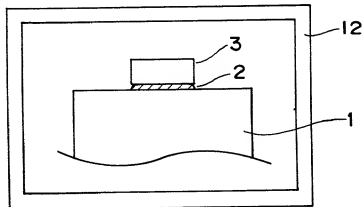


Fig.3

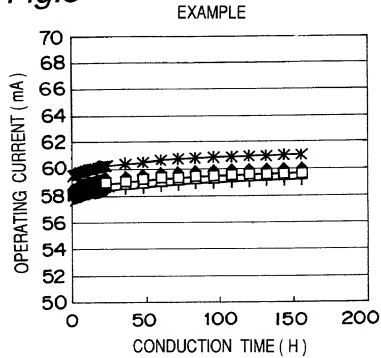


Fig.4

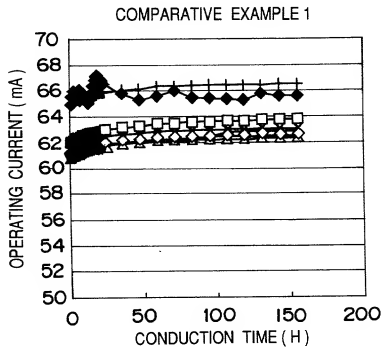


Fig.5

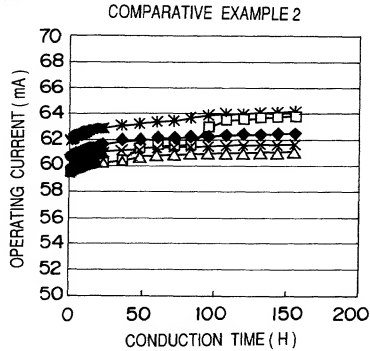


Fig.6

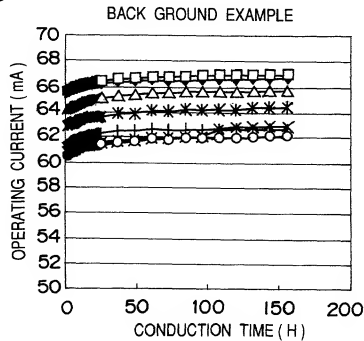


Fig.7 BACK GROUND ART

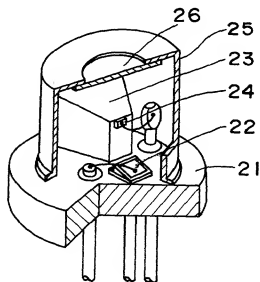
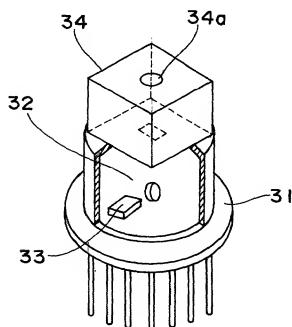


Fig.8 BACK GROUND ART



Morrison & Foerster LLP
2000 Pennsylvania Avenue, N.W.
Washington, D.C. 20006-1888
(202) 887-1500

Sheet 6 of 7

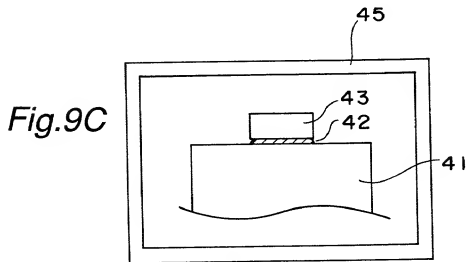
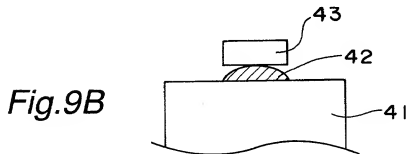
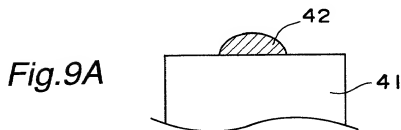


Fig.10A

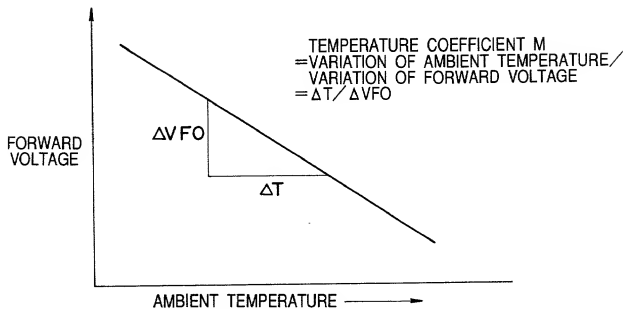


Fig.10B

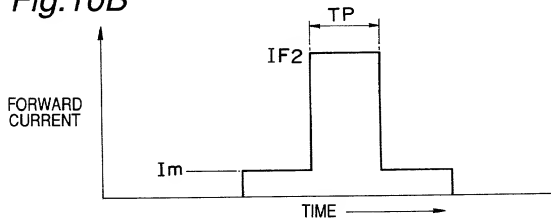
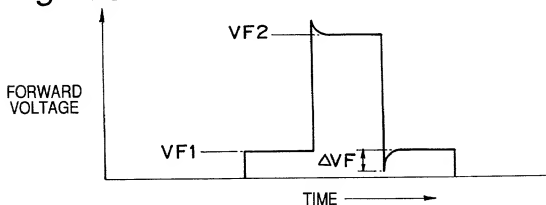


Fig.10C



PATENT
Docket No.

Client Ref.

**COMBINED DECLARATION AND POWER OF ATTORNEY
FOR UTILITY/DESIGN PATENT APPLICATION**

AS A BELOW-NAMED INVENTOR, I HEREBY DECLARE THAT:

My residence, citizenship, and post office address are as stated below next to my name.

I believe I am the original, first and sole (or joint, if more than one name appears below) inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled:

SEMICONDUCTOR LASER MANUFACTURING METHOD AND
SEMICONDUCTOR LASER

the specification of which:

- ☒ is attached hereto.
☐ was filed on _____ as application serial No. _____ and was amended
on _____ (if applicable).

I HAVE REVIEWED AND UNDERSTAND THE CONTENTS OF THE ABOVE-
IDENTIFIED SPECIFICATION, INCLUDING THE CLAIMS, AS AMENDED BY ANY
AMENDMENT REFERRED TO ABOVE.

I acknowledge and understand that I have a duty to disclose information which is material to the patentability of the claims of this application in accordance with Title 37, Code of Federal Regulations, §§ 1.56(a) and (b).

I hereby claim foreign priority benefits under Title 35, United States Code § 119(a)-(d) of the foreign application(s) for patent indicated below and have also identified below the foreign applications for patent or inventor's certificate on this invention having a filing date before that of the application for patent or inventor's certificate on this invention having a filing date before that of the application on which priority is claimed:

03987010-111301

Country/International:	Application No.	Date of Filing (day/month/year)	Priority Claimed?
Japan	2000-354191	21/11/2000	<input checked="" type="checkbox"/> Yes <input type="checkbox"/> No.
			<input type="checkbox"/> Yes <input type="checkbox"/> No.
			<input type="checkbox"/> Yes <input type="checkbox"/> No.
			<input type="checkbox"/> Yes <input type="checkbox"/> No.
			<input type="checkbox"/> Yes <input type="checkbox"/> No.

Antoinette F. Konski (Reg. No. 34,202)
E. Victor Donahue (Reg. No. 35,492)
Laurie Axford (Reg. No. 35,053)
Catherine M. Polizzi (Reg. No. 40,130)
Thomas D. Mays (Reg. No. 34,524)
Richard D. Jordan (Reg. No. 33,519)

Harry J. Macey (Reg. No. 32,818)
Robert Saltzberg (Reg. No. 36,910)
Mani Adeli (Reg. No. 39,585)
Sean Brennan (Reg. No. 39,917)
J. Michael Schiff (Reg. No. 40,253)

Please direct all communications to:

Barry E. Bretschneider
Morrison & Foerster LLP
2000 Pennsylvania Avenue, N.W.
Washington, D.C. 20006-1888

Please direct all telephone calls to Barry E. Bretschneider at (202) 887-1500.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under § 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Oct. 31, 2001

Date

Tetsuyoshi Inoue

Name: Tetsuyoshi INOUE

Residence: Yamatotakada-shi, Nara-ken, Japan

Citizenship: Japan

Post Office Address: 2-3-52-109, Nishimikurado, Yamatotakada-shi,
Nara-ken, Japan

Oct. 31, 2001

Date

Kazunori Matsubara

Name: Kazunori MATSUBARA

Residence: Shiki-gun, Nara-ken, Japan

Citizenship: Japan

Post Office Address: 537, Yakuoji, Tawaramoto-cho, Shiki-gun,
Nara-ken, Japan

Date

Name:

Residence:

Citizenship:

Post Office Address: